

YO998-426DIV

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re divisional patent application of

Chan et al.

Serial No.: Not yet assigned

Group Art Unit: Unknown

Filed: Concurrently herewith

Examiner: Unknown

For: SELF-ALIGNED DOUBLE-GATE MOSFET BY SELECTIVE EPITAXY  
AND SILICON WAFER BONDING TECHNIQUES

Assistant Commissioner of Patents  
Washington, D.C. 20231

**PRELIMINARY AMENDMENT**

Sir:

Prior to examination on the merits and calculation of the filing fee, please amend the  
above-identified application as follows:

**IN THE SPECIFICATION:**

Page 1, after line 3, insert the following:

Cross-Reference To Related Applications

This application is a division of U.S. Application Serial Number 09/272,297 filed

March 19, 1999.

Please replace the paragraph appearing on page 4, lines 11-16 of the application with  
the following paragraph.

There are two different issues important to this aspect of the invention. First the  
introduction of impurities is for the purpose of limiting the diffusion. For example,  
introduction of carbon reduces boron diffusion. Secondary, forming an alloy such as  $\text{Si}_x\text{Ge}_{1-x}$

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